

Contents

1	Introduction	1
1.1	Motivation	1
1.2	State of the Art of USJ Characterization	3
1.2.1	Contacting and/or Destructive Techniques	3
1.2.2	Non-Contacting and Non-Destructive Techniques	10
1.3	Outline	16
	References	17
2	Theory of Perturbation of the Reflectance	21
2.1	Uniform Perturbation of the Complex Refractive Index	25
2.2	Box-Like Perturbation of the Complex Refractive Index	26
2.3	Double Box-Like Perturbation of the Complex Refractive Index	28
2.4	Arbitrary Perturbation of the Complex Refractive Index	31
2.5	Second-Order Effects	33
2.5.1	Impact of the Presence of a Native Oxide	33
2.5.2	Impact of a Lateral Variation in Refractive Index Perturbation	35
2.6	Summary	36
	References	37
3	Theory of Perturbation of the Refractive Index	39
3.1	Refractive Index of Electrically Conductive Materials	41
3.2	Electrooptical Effects	42
3.2.1	Drude Effect	42
3.2.2	Carrier-Induced Bandgap Narrowing (BGN) Effect	43
3.2.3	Burstein Shift or Band-Filling (BF) Effect	47
3.2.4	Pockels, Kerr and Franz-Keldysh Effects	48

3.3	Thermooptical Effects	48
3.4	Summary	49
	References	50
4	Theory of Carrier and Heat Transport in Homogeneously Doped Silicon	53
4.1	Thermodynamic Model	55
4.1.1	Generalized Ambipolar Diffusion Equation	58
4.1.2	Heat Equation.	62
4.1.3	Steady-Periodic Model Equations	63
4.1.4	Summary	76
4.2	Solutions	78
4.2.1	One-Dimensional Linear Solution	79
4.2.2	Three-Dimensional Linear Solution	83
4.2.3	Three-Dimensional Nonlinear Solution	92
4.3	Summary	95
	References	98
5	Extension of the Transport Theory to Ultra-Shallow Doped Silicon Layers	101
5.1	Simplified Transport Theory	103
5.2	Validity of the Assumptions	106
5.2.1	Flat Quasi-Fermi Level Approximation	107
5.2.2	Impact of Doped Layers on Substrate Injection	109
5.3	Steady-Periodic Model Equations	110
5.4	Summary	113
	References	113
6	Assessment of the Model	115
6.1	Homogeneous Doping	118
6.1.1	Comparison of the Model with Experimental Data	119
6.2	Box-Like Doping Profile	124
6.2.1	Comparison of the Model with Experimental Data	126
6.3	Discussion of the Modeling Error	133
6.3.1	Modeling Error on R_{dc}	133
6.3.2	Modeling Error on ΔR_{ac}	134
6.4	Summary	137
	References	138
7	Application of the Model to Carrier Profiling	141
7.1	Model-Free Determination of Junction Depths	141
7.1.1	Absolute Determination of Junction Depths	142
7.1.2	Relative Determination of Junction Depths	149

- 7.2 Model-Based Profile Characterization Technique. 158
 - 7.2.1 Fundamental Principle of the Technique 159
 - 7.2.2 Implementation of the Technique 161
 - 7.2.3 Discussion of the Results 163
- 7.3 Summary 170
- References 171

- 8 Conclusions and Recommendations. 173**
 - 8.1 Development of the Model 173
 - 8.2 Evaluation of the Model. 174
 - 8.3 Application of the Model 175
 - 8.4 Future Work 176

- Appendix 179**

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